

650V N-Channel Enhancement Mode MOSFET

Description

The AP2N65D/Y is silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency.

General Features

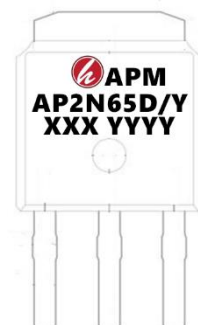
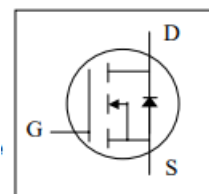
$V_{DS} = 650V, I_D = 2A$

$R_{DS(ON)} < 4.8\Omega @ V_{GS} = 10V$

Application

Uninterruptible Power Supply(UPS)

Power Factor Correction (PFC)



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP2N65D	TO-252-3L	AP2N65D XXX YYYY	2500
AP2N65Y	TO-251-3L	AP2N65Y XXX YYYY	4000

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	650	V
Continuous Drain Current	I_D	2	A
Pulsed Drain Current	I_{DM}	6	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulse Avalanche Energy	E_{AS}	57	mJ
Avalanche Current	I_{AR}	2.4	A
Repetitive Avalanche Energy	E_{AR}	6.4	mJ
Power Dissipation ($T_C = 25^\circ C$)	P_D	25	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ C$
Thermal Resistance, Junction-to-Case	R_{thJC}	5	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	60	

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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^{\circ}\text{C}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1.0A$	--	4	4.8	Ω
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V, f = 1.0\text{MHz}$	--	310	--	pF
Output Capacitance	C_{oss}		--	39	--	
Reverse Transfer Capacitance	C_{rss}		--	6	--	
Total Gate Charge	Q_g	$V_{DD} = 520V, I_D = 2.0A,$ $V_{GS} = 10V$	--	8.0	--	nC
Gate-Source Charge	Q_{gs}		--	1.2	--	
Gate-Drain Charge	Q_{gd}		--	5	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 300V, I_D = 2.0A,$ $R_G = 25\Omega$	--	7.8	--	ns
Turn-on Rise Time	t_r		--	33	--	
Turn-off Delay Time	$t_{d(off)}$		--	23	--	
Turn-off Fall Time	t_f		--	59	--	
Continuous Body Diode Current	I_S	$T_C = 25^{\circ}\text{C}$	--	--	2	A
Pulsed Diode Forward Current	I_{SM}		--	--	8	
Body Diode Voltage	V_{SD}	$T_J = 25^{\circ}\text{C}, I_{SD} = 2.0A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 2.0A,$ $di_F/dt = 100A/\mu s$	--	80	--	ns
Reverse Recovery Charge	Q_{rr}		--	1.8	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 2.4A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

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Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

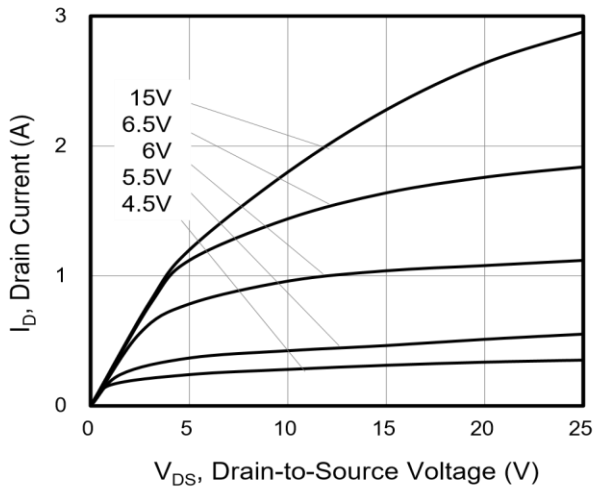


Figure 2. Body Diode Forward Voltage

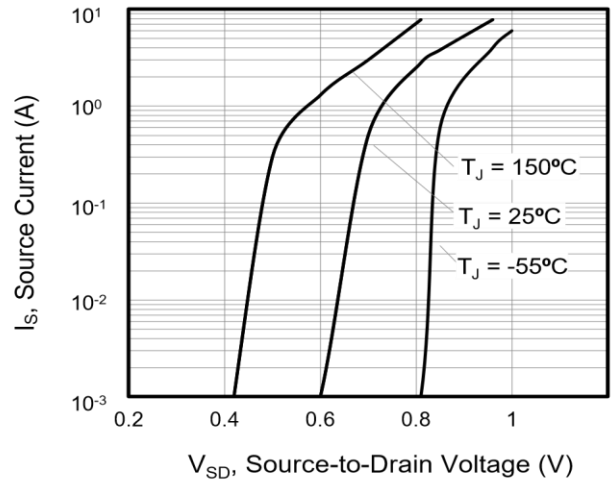
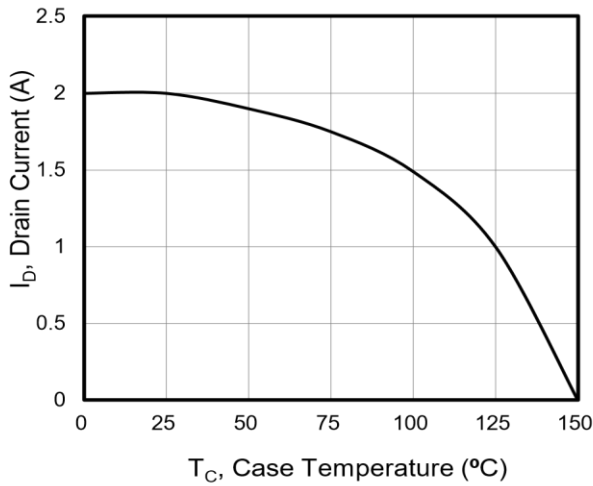


Figure 3. Drain Current vs. Temperature



**Figure 4. Power Dissipation vs. Temperature
TO-251, TO-252**

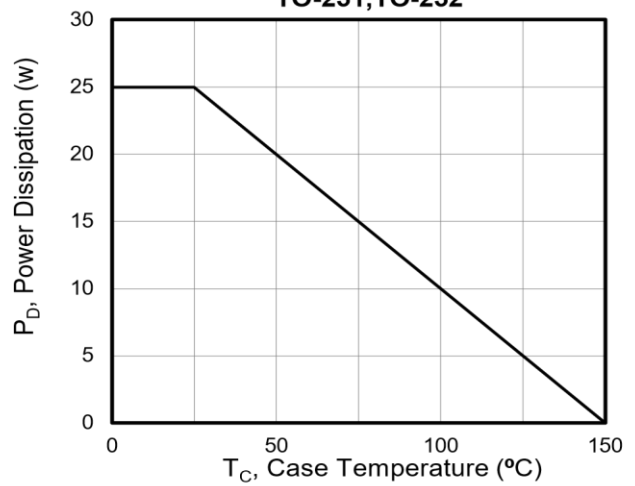


Figure 5. Transfer Characteristics

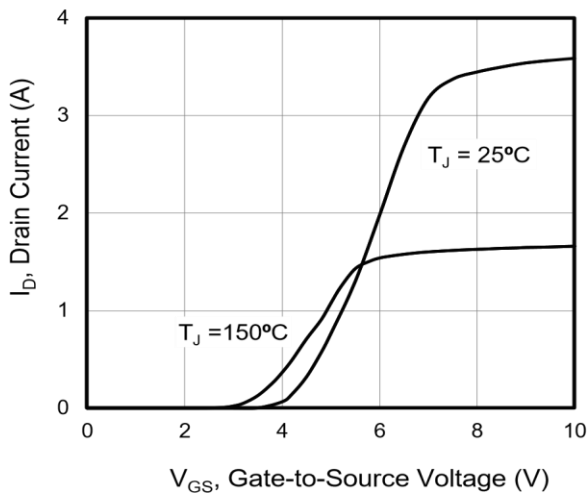


Figure 6. On-Resistance vs. Temperature

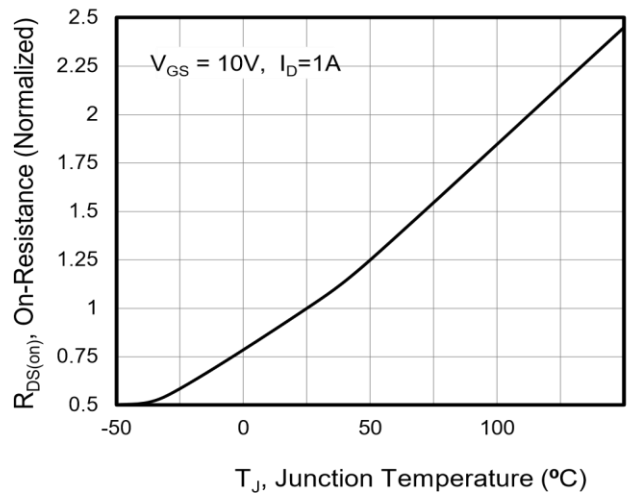


Figure 7. Capacitance

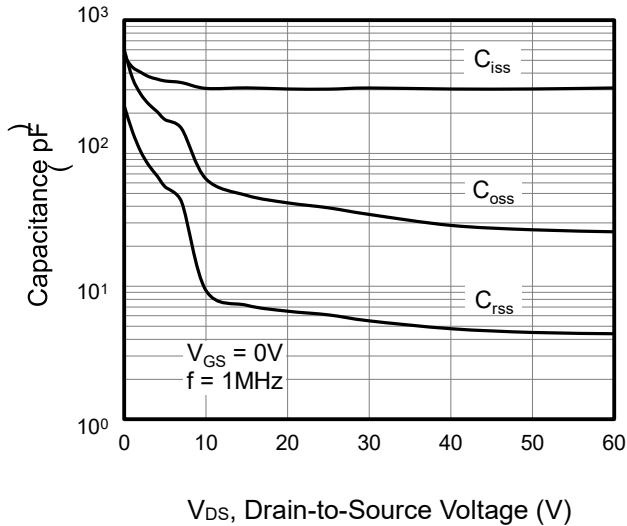
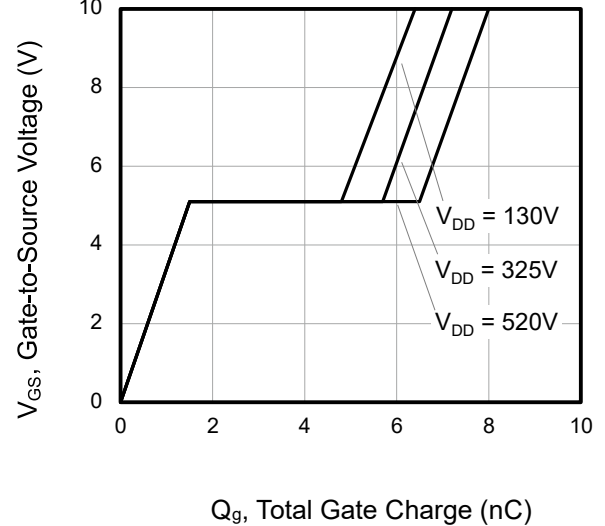
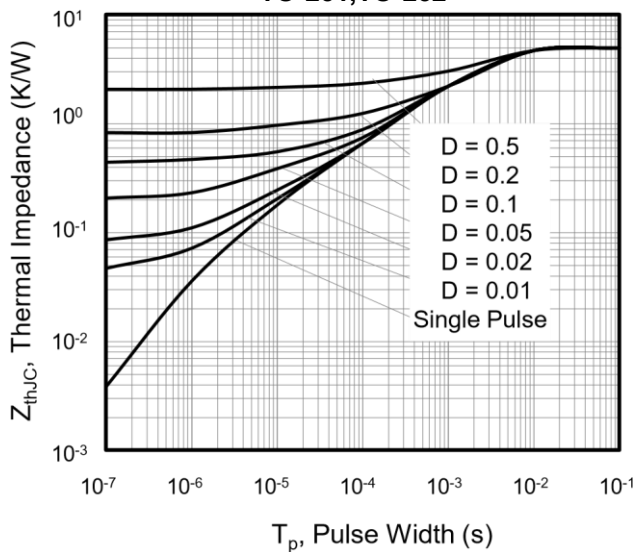


Figure 8. Gate Charge



**Figure 9. Transient Thermal Impedance
TO-251, TO-252**



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Figure A: Gate Charge Test Circuit and Waveform

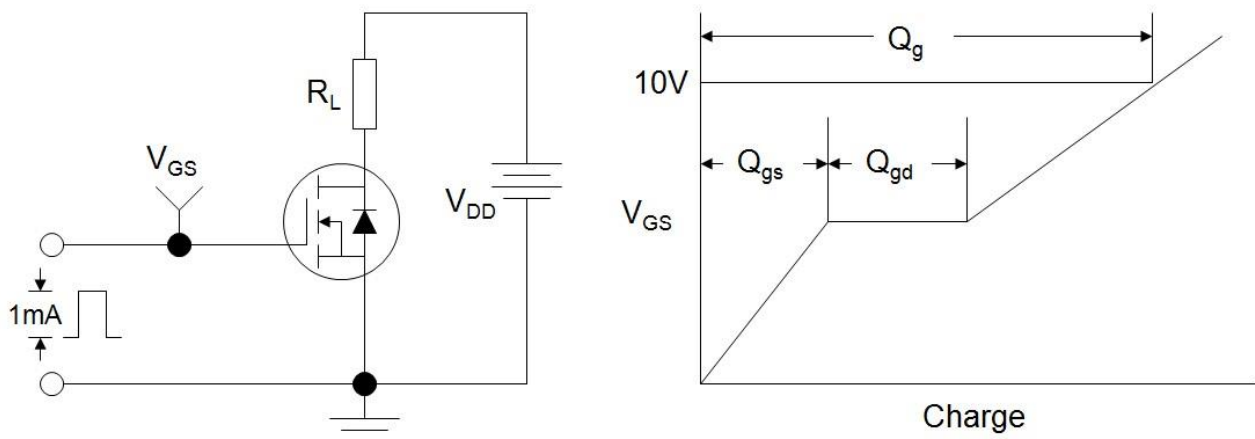


Figure B: Resistive Switching Test Circuit and Waveform

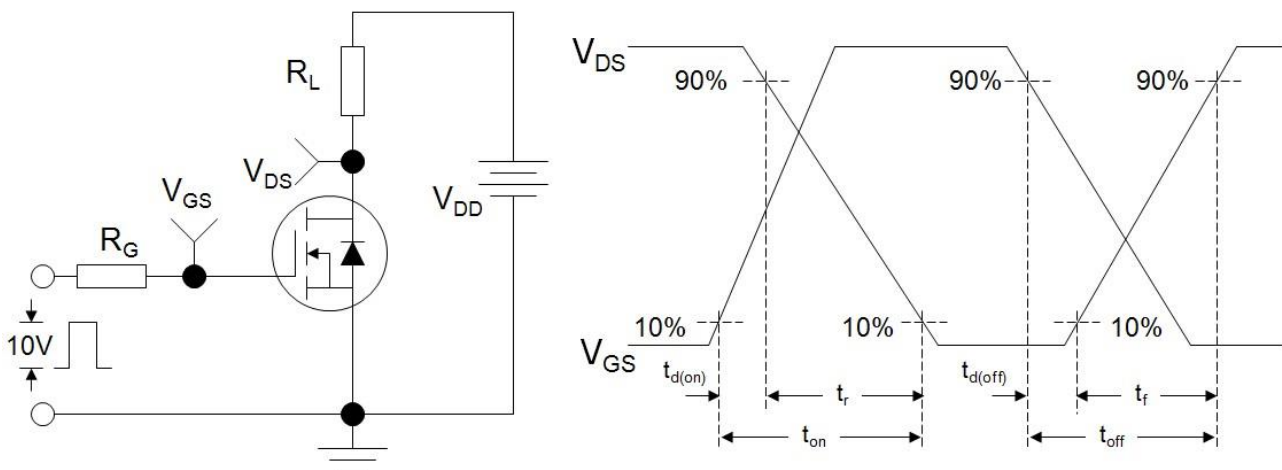
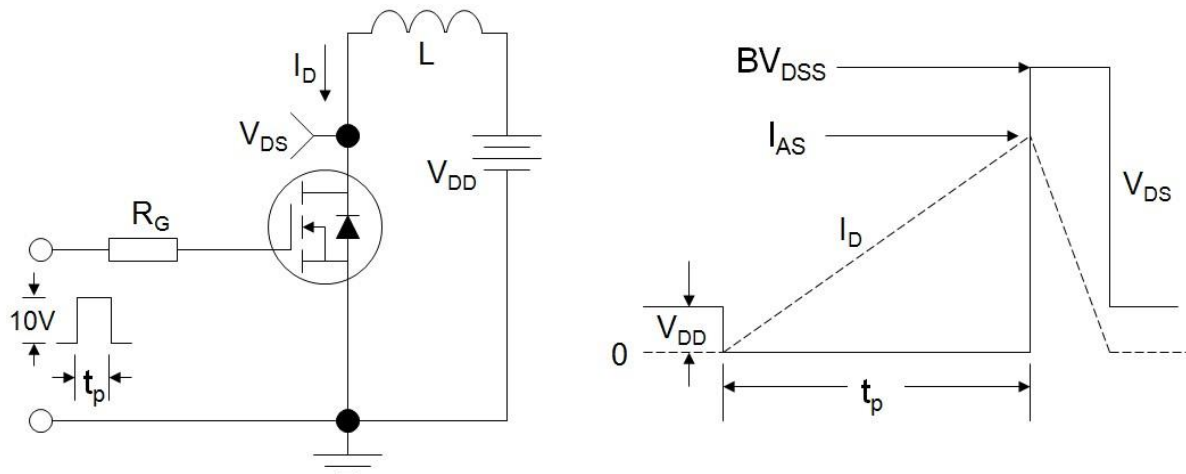
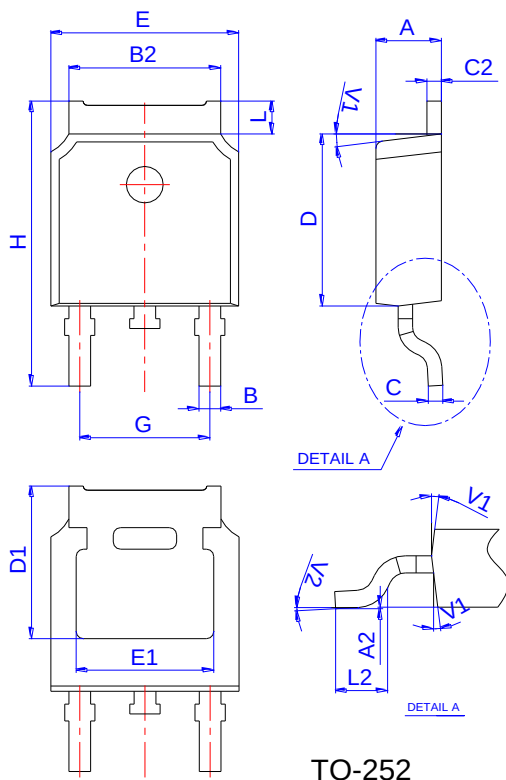


Figure C: Unclamped Inductive Switching Test Circuit and Waveform

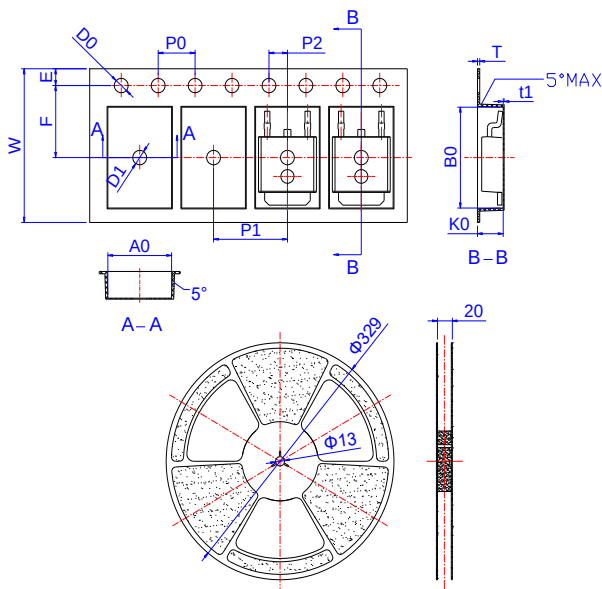


Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

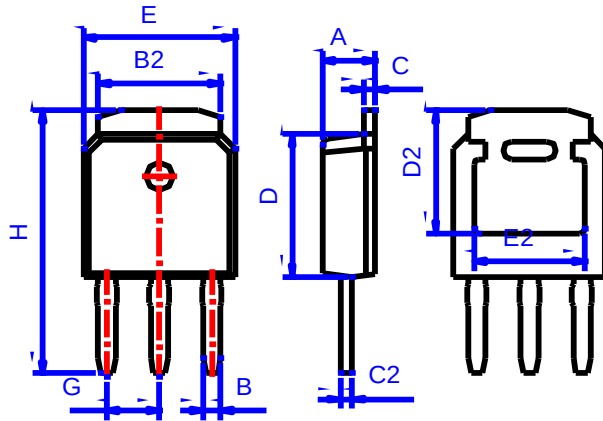
Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TAPING	2,500	25,000	13inch

Package Mechanical Data



TO-251S

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10	2.30	2.50	0.083	0.091	0.098
B	0.66	0.76	0.86	0.026	0.030	0.034
B2	5.15	5.33	5.48	0.203	0.210	0.216
C	0.44	0.51	0.58	0.017	0.020	0.023
C2	0.44	0.51	0.58	0.017	0.020	0.023
D	5.90	6.10	6.30	0.232	0.240	0.248
D2	5.30 REF			0.209 REF		
E	6.40	6.60	6.80	0.252	0.260	0.268
E2	4.83 REF			0.190 REF		
G	2.19	2.29	2.39	0.086	0.090	0.094
H	10.60	11.20	11.80	0.417	0.441	0.465

Package Information-TO-251S

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	80	4,000	32,000

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